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Consequences of Long Term Transients in Large Area High Density Plasma Processing: A 3-Dimensional Computational Investigation*

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- Introduction
- Description of 3-dimensional parallel hybrid model
- Consequences of asymmetric pumping
- Pulsed operation of ICPs
- Summary

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300MM WAFER PROCESSING: CHALLENGES

- Side-to-side asymmetries in plasma properties become more critical as wafer size increases.
- Side pumping and side gas injection are common in industrial reactors and can lead to asymmetries in species densities, fluxes and temperatures.
- Flow asymmetries become pronounced when feedback through plasma conductivity make the inductive fields and power deposition non-uniform.
- In this work, we investigate the effect of long term transients such as during pulsed operation of ICPs on flow induced asymmetries.

HYBRID PLASMA EQUIPMENT MODEL (HPEM-3D)

 Hybrid Plasma Equipment Model (HPEM-3D) is a modular simulator to address low temperature plasmas.



• Continuity (heavy species) :

$$\frac{\partial \mathbf{N}_{i}}{\partial t} = \nabla \cdot \left(\mathbf{N}_{i} \vec{\mathbf{v}}_{i} \right) + \mathbf{S}_{i}$$

• Momentum (heavy species) :

$$\frac{\partial (N_i \vec{v}_i)}{\partial t} = \frac{q_i}{m_i} N_i (\vec{E}_s + \vec{v}_i \times \vec{B}_s) - \frac{1}{m_i} \nabla P_i - \nabla \cdot (N_i \vec{v}_i \vec{v}_i) - \nabla \cdot \overline{\overline{\tau}}_i + \sum_j N_i N_j k_{ij} (\vec{v}_j - \vec{v}_i)$$

• Energy (heavy species) :

$$\frac{\partial \mathbf{N}_{i} \mathbf{c}_{V} \mathbf{T}_{i}}{\partial t} = \nabla \cdot \kappa_{i} \nabla \mathbf{T}_{i} - \mathbf{P}_{i} \nabla \cdot \vec{\mathbf{v}}_{i} - \nabla \cdot (\vec{\phi}_{i} \varepsilon_{i}) + \frac{\mathbf{N}_{i} q_{i}^{2}}{m_{i} v_{i}} \mathbf{E}_{s}^{2} + \frac{\mathbf{N}_{i} q_{i}^{2} v_{i}}{m_{i} (v_{i}^{2} + \omega^{2})} \mathbf{E}^{2}$$

• Drift-diffusion (electron) :

 $\frac{\partial n_{e}}{\partial t} = \nabla \cdot \left(n_{e} \overline{\overline{\mu}}_{e} E_{s} + \overline{\overline{D}}_{e} \nabla n_{e} \right) + S_{e}$

GOVERNING EQUATIONS IN HPEM-3D

- Electron energy transport is addressed by solving the electron energy equation coupled with a solution of Boltzmann's equation for transport coefficients.
- Electron energy:

$$\nabla \cdot k \nabla T_{e} + \nabla \cdot (\Gamma T_{e}) = P_{heating} - P_{hoss}$$

• Poisson's equation :

$$\nabla \cdot \varepsilon \nabla \Phi(t + \Delta t) = \rho(t) + \frac{d\rho(t)}{dt} = \rho(t) + \sum_{i} q_{i} \Delta t [-\nabla \cdot \vec{\varphi}_{i} + S_{i}]$$

• Wave equation :

$$\nabla \cdot \frac{1}{\mu} \nabla E = \frac{\partial^2 \left(\epsilon_0 E \right)}{\partial t^2} + \frac{\partial \left(\overline{\overline{\sigma}} E + J_0 \right)}{\partial t}$$

REACTOR GEOMETRY AND SIMULATION CONDITIONS

- 2-turn symmetric coil, showerhead and an asymmetric pump port
- Base case conditions:
- Power: 600 W, 10 MHz
- Flow rate: 160 sccm
- Pressure: 5 mTorr
- Ar, C_2F_6/CF_4

Height-A: Densities, Temperatures, Fluxes Height-B: ICP power, Conductivity, Sources



SYMMETRIC CASE: PLASMA PROPERTIES



- Power is deposited beneath the coils within the skin depth.
- T_e peaks in the skin depth due to positive power deposition from inductive fields.
- Electron density peaks off-center in the bulk of the plasma.
- C₂F₆/CF₄ (40/60), 600 W, 5 mTorr, 160 sccm

CONTINUOUS WAVE (CW) OPERATION OF ICPS

- Flow induced non-uniformities in reaction sources make ion density non-uniform.
- Non-uniform plasma conductivity make the inductive fields and power deposition non-uniform even with symmetric coils.
- Non-uniform power deposition reinforces the asymmetries in reaction sources.
- This feedback loop during CW operation strengthens flow induced asymmetries.



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PLASMA CONDUCTIVITY AND POWER DEPOSITION



- As a result of asymmetric pumping, the plasma conductivity is azimuthally asymmetric even at the plane below the showerhead.
- Reaction sources are non-uniform with a maximum away from the pump port.

ASYMMETRIC ELECTRON AND RADICAL DENSITIES



- Larger reaction sources result in larger ion and radical densities opposite to the pump port.
- Wall recombination results in a virtual asymmetric source of CF₂.

PULSED OPERATION OF ICPS



PULSED INDUCTIVELY COUPLED PLASMAS

- Pulsed plasmas
 - Plasma etching with better uniformity and anisotropy
 - Improved etch selectivity by modifying the ratio of chemical species
 - Reduce charge buildup on wafers and suppress notching
- Current models for investigating pulsed operation are typically global or 1-dimensional.
- Difficult to resolve long-term transients in multi-dimensional plasma equipment models.
- Moderately parallel algorithms for 2-D and 3-D hybrid models were developed to investigate long term transients.

DESCRIPTION OF PARALLEL HYBRID MODEL

- The HPEM, a modular simulator, was parallelized by employing a shared memory programming paradigm on a Symmetric Multi-Processor (SMP) machine.
- The Electromagnetics, Electron Monte Carlo and Fluid-kinetics Modules are simultaneously executed on three processors.
- The variables updated in different modules are immediately made available through shared memory for use by other modules.



PULSED OPERATION OF ICPS

- Pulsed plasma is a rf discharge in which the ICP power is pulsesquare wave modulated.
- Flow asymmetries also become pronounced when feedback through plasma conductivity make power deposition nonuniform.
- Pulsed operation of ICPs may aid in reducing these asymmetries.



TEMPORAL DYNAMICS OF PULSED PLASMAS



- As the duty cycle increases, the reactor average electron density in the activeglow increases.
- Electron density in the activeglow increases with decrease in 5 KHz as the ICP power is ON for longer duration.

• Ar, 600 W, 5 mTorr, 160 sccm, PRF: 10 kHz, 50% Pramod_ispc_16

PULSED ICPS: SYMMETRIC PUMPING



- Utilizing the plane of symmetry, the simulations need to be performed only for 180°.
- With symmetric pumping, the plasma properties are azimuthally symmetric. Ar⁺ density peaks in the center of the discharge.
- The power deposition is also symmetric.

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Animation slide

PULSED ICPS: ASYMMETRIC PUMPING

- At the wafer plane, density and source function of Ar⁺ ions are asymmetric during CW operation.
- By pulsing, asymmetries at the wafer plane are reduced.
- During the afterglow, diffusion smoothens the plasma density profile.
- In pulsed ICPs, feedback between non-uniform densities and power deposition is reduced.









PULSED ICPS: ASYMMETRIC PUMPING

<u>cm⁻³</u> 3 X 10¹¹

Wcm⁻³ 2.2

- During CW operation, though the coils are symmetric, ICP power deposition is non uniform.
- ICP power peaks at regions of larger plasma conductivity owing to a larger electron density.
- With 50% duty cycle, ICP power is off during 50% of the pulse period.
- In the absence of non-uniform sources, the plasma becomes more uniform in the afterglow.

3 X 10⁹

0.05





EFFECT OF DUTYCYCLE: Ar⁺ DENSITY



- As the duty cycle decreases, the ICP power is OFF for longer duration.
- Hence the reduced feedback and increased diffusion make the time averaged ion density more uniform.
- Radial plasma uniformity is better at a duty cycle of 70% compared to 30%.

TIME AVERAGED PLASMA PROPERTIES

- The pulsed operation of ICP makes the power deposition more uniform compared to CW.
- On a time average basis, the ion density is more uniform.
- The flux of ions impinging the wafer will be more symmetric.
- Hence the etch or deposition profiles will be more uniform at different azimuths on the wafer.





- A new 3-D parallel hybrid model was developed to address transients based on moderate computational parallelism.
- Reactor scale asymmetries can result in non-uniform trench evolution during fluorocarbon etching at different azimuthal locations.
- During pulsed operation, diffusion smoothens the plasma density profile in the afterglow, providing a more uniform set of initial conditions for the next power pulse.
- The feedback between non-uniform densities and power deposition is also reduced.
- The flux of ions impinging the wafer will be more symmetric during pulsed operation.